

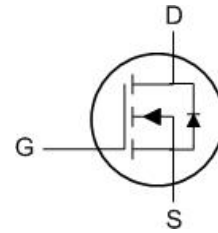


- ★ 100% EAS Guaranteed
- ★ Green Device Available
- ★ Excellent CdV/dt effect decline
- ★ Advanced VD MOSFETS

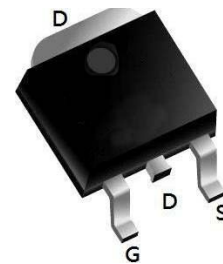
Description

The WLU5N50 is the Advanced VD N-ch MOSFETS, which provide excellent RDSON and gate charge for most of the synchronous buck converter applications.

The WLU5N50 meet the RoHS and Green Product requirement 100% EAS guaranteed with full function reliability approved.



TO252 Pin Configuration



Product Summary

BVDSS	RDSON	ID
500V	1.45mΩ	5A

Absolute Maximum Ratings

Symbol	Parameter	Value	Units
V _{DSS}	Drain-Source Voltage	500	V
I _D	Drain Current - Continuous (TC= 25°C) - Continuous (TC= 100°C)	5	A
		2.6*	A
I _{DM}	Drain Current - Pulsed (Note 1)	20*	A
V _{GSS}	Gate-Source Voltage	± 30	V
E _{AS}	Single Pulsed Avalanche Energy (Note 2)	167	mJ
I _{AR}	Avalanche Current (Note 1)	5	A
E _{AR}	Repetitive Avalanche Energy (Note 1)	10.6	mJ
dv/dt	Peak Diode Recovery dv/dt (Note 3)	5	V/ns
P _D	Power Dissipation (TC = 25°C) - Derate above 25°C	24.5	W
		0.2	W/°C
T _j , T _{stg}	Operating and Storage Temperature Range	-55 to +150	°C
T _L	Maximum lead temperature for soldering purposes, 1/8" from case for 5 seconds	300	°C

Thermal Characteristics

Symbol	Parameter	Value	Units
R _{θJC}	Thermal Resistance, Junction-to-Case	4.20	°C/W
R _{θJS}	Thermal Resistance, Case-to-Sink Typ.	--	°C/W
R _{θJA}	Thermal Resistance, Junction-to-Ambient	48.2	°C/W



Electrical Characteristics TC = 25°C unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0\text{ V}, I_D = 250\ \mu\text{A}$	500			V
$\Delta BV_{DSS} / \Delta T_J$	Breakdown Voltage Temperature Coefficient	$I_D = 250\ \mu\text{A}$, Referenced to 25°C		0.49		V/°C
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 500\text{ V}, V_{GS} = 0\text{ V}$			1	μA
		$V_{DS} = 400\text{ V}, TC = 125^\circ\text{C}$			10	μA
I_{GSSF}	Gate-Body Leakage Current, Forward	$V_{GS} = 30\text{ V}, V_{DS} = 0\text{ V}$			100	nA
I_{GSSR}	Gate-Body Leakage Current, Reverse	$V_{GS} = -30\text{ V}, V_{DS} = 0\text{ V}$			-100	nA
On Characteristics						
$V_{GS(TH)}$	Gate Threshold voltage	$V_{DS}=V_{GS}, I_D=250\ \mu\text{A}$	2.0		4.0	V
$R_{DS(On)}$	Drain-Source on-state resistance	$V_{GS}=10\text{ V}, I_D = 2\text{ A}, T_J = 25^\circ\text{C}$		1.45	1.8	Ω
g_{FS}	Forward Transconductance	$V_{DS} = 40\text{ V}, I_D = 2.5\text{ A}$ (Note 4)		2.90		S
Dynamic Characteristics						
C_{iss}	Input capacitance	$V_{DS} = 25\text{ V}, V_{GS} = 0\text{ V}, f = 1.0\text{ MHz}$		415		pF
C_{oss}	Output capacitance			58		pF
C_{riss}	Reverse transfer capacitance			1.4		pF
Switching Characteristics						
$t_{d(on)}$	Turn On Delay Time	$V_{DD} = 250\text{ V}, I_D = 5\text{ A}, R_G = 25\ \Omega$ (Note 4, 5)		7		ns
t_r	Rising Time			22		ns
$t_{d(off)}$	Turn Off Delay Time			15		ns
t_f	Fall Time			23		ns
Q_g	Total Gate Charge	$V_{DS} = 400\text{ V}, I_D = 5\text{ A}, V_{GS} = 10\text{ V}$ (Note 4, 5)		13		nC
Q_{gs}	Gate-Source Charge			4.9		nC
Q_{gd}	Gate-Drain Charge			2.3		nC
Drain-source Diode Characteristics and Maximum Ratings						
I_S	Maximum continuous Drain-source Diode Forward Current				5	A
I_{SM}	Maximum Pulsed Drain-Source Diode Forward Current				20	A
V_{SD}	Diode Forward Voltage	$V_{GS}=0\text{ V}, I_S = 5\text{ A}$			1.2	V
t_{rr}	Reverse Recovery Time	$V_{GS} = 0\text{ V}, I_S = 5\text{ A}, di_F / dt = 100\text{ A}/\mu\text{s}$ Note 4)		289		ns
Q_{rr}	Reverse Recovery Charge				1.2	

Notes:

1. Repetitive Rating : Pulse width limited by maximum junction temperature
2. L = 10.6 mH, IAS = 5 A, VDD = 50V, RG = 25 Ω , Starting TJ = 25°C
3. ISD ≤ 5A, di/dt ≤ 200A/us, VDD ≤ BVDSS, Starting TJ = 25°C
4. Pulse Test : Pulse width ≤ 300us, Duty cycle ≤ 2%
5. Essentially independent of operating temperature



Typical Characteristics

Table 7 Reverse diode characteristics

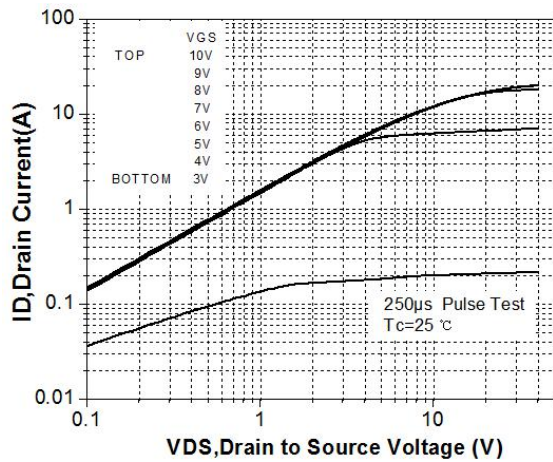


Figure 1. On-Region Characteristics

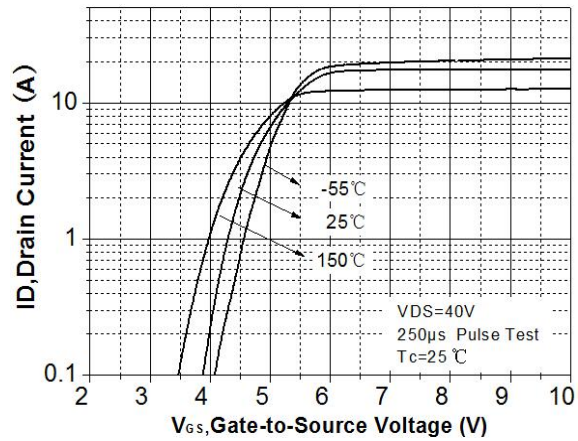


Figure 2. Transfer Characteristics

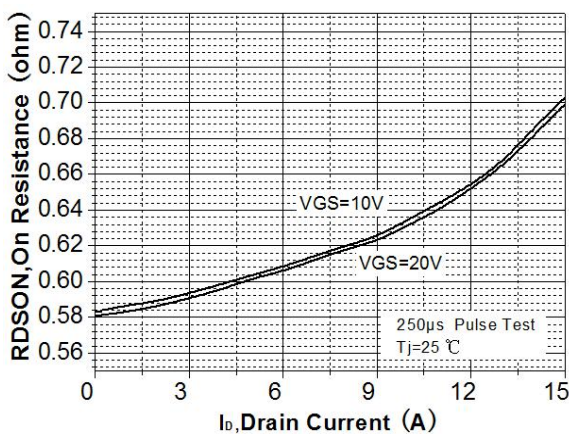


Figure 3. On-Resistance Variation vs Drain Current and Gate Voltage

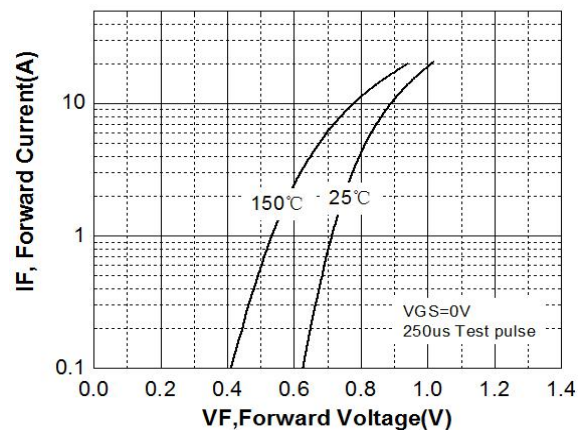


Figure 4. Body Diode Forward Voltage Variation with Source Current and Temperature

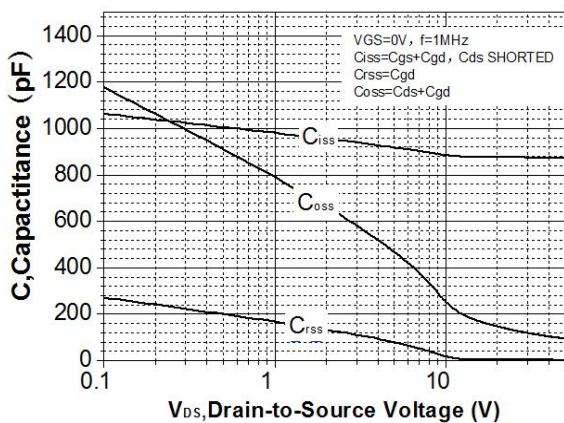


Figure 5. Capacitance Characteristics

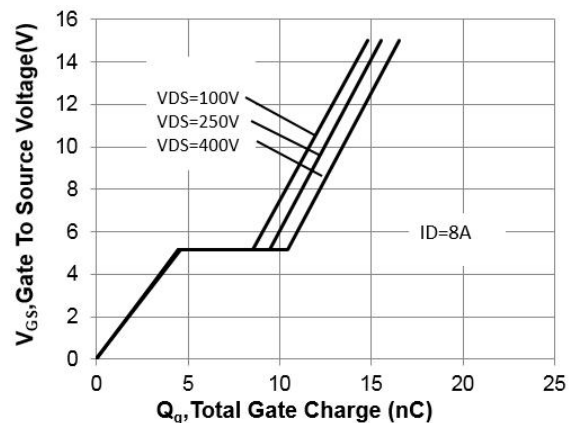


Figure 6. Gate Charge Characteristics



Typical Characteristics (Continued)

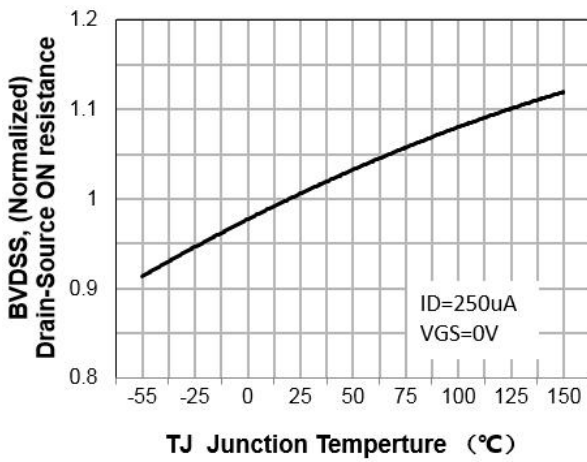


Figure 7. Breakdown Voltage Variation vs Temperature

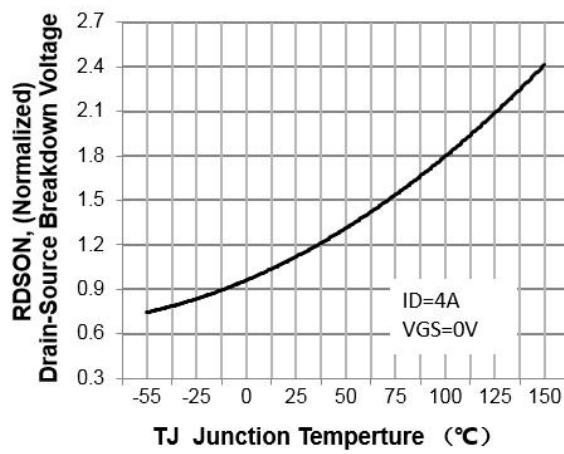


Figure 8. On-Resistance Variation vs Temperature

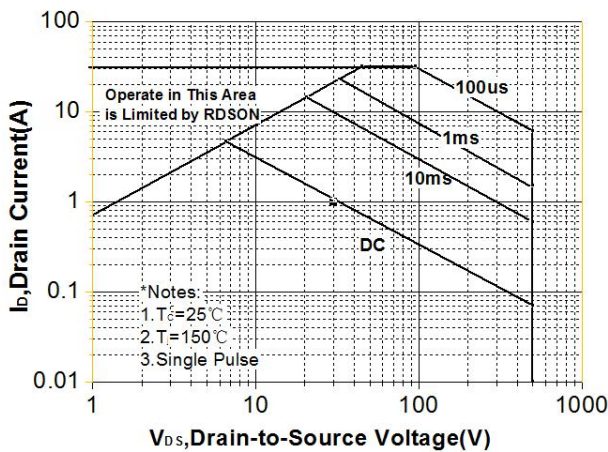


Figure 9. Maximum Safe Operating Area

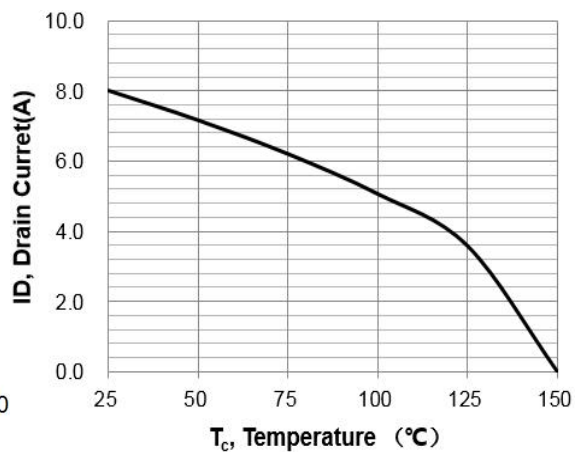


Figure 10. Maximum Drain Current vs Case Temperature

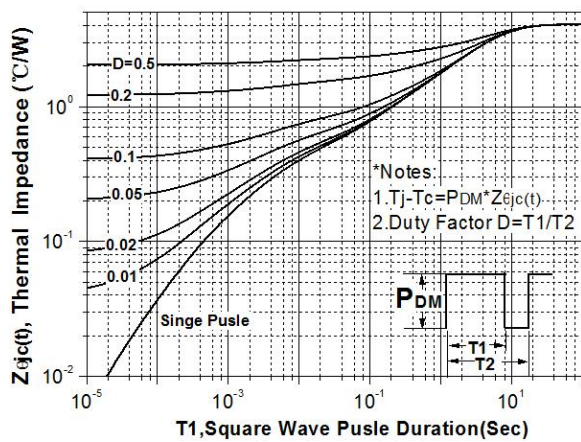
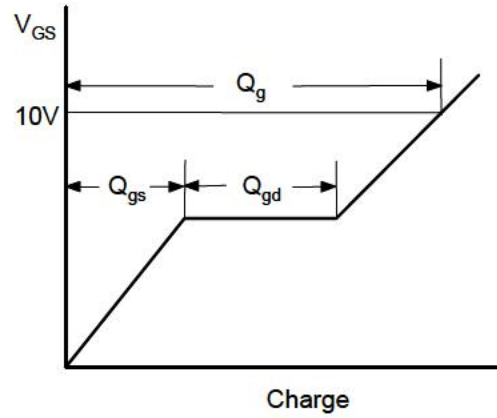
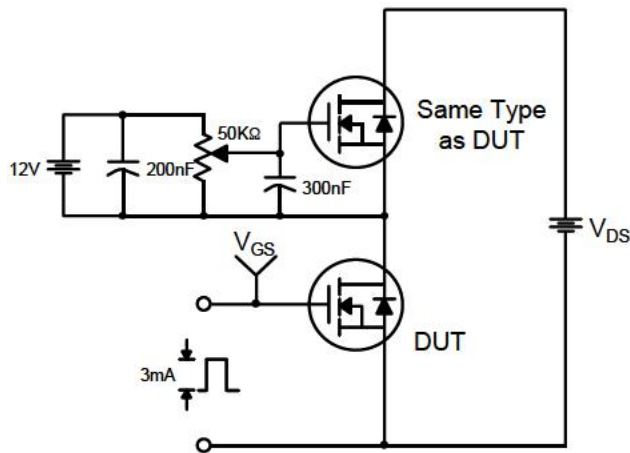


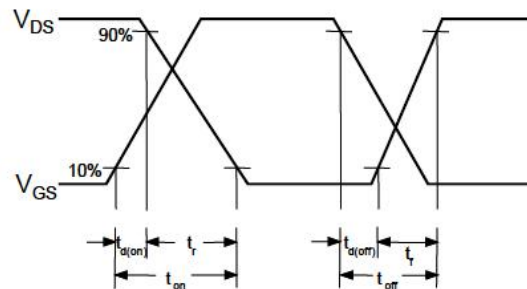
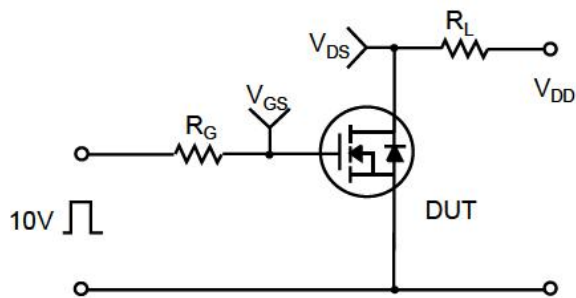
Figure 11. Transient Thermal Response Curve



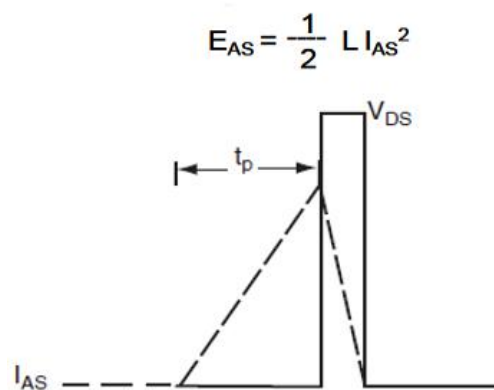
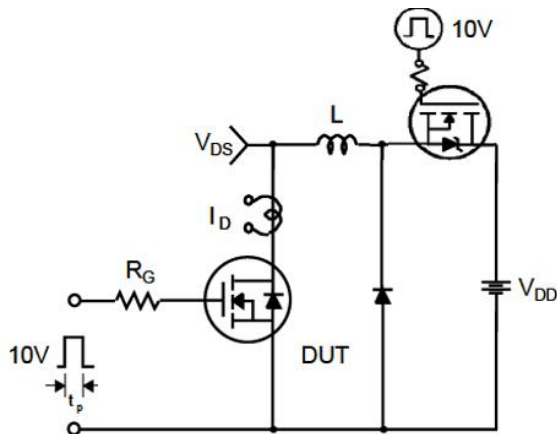
Gate Charge Test Circuit & Waveform



Resistive Switching Test Circuit & Waveforms



Unclamped Inductive Switching Test Circuit & Waveforms





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